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THE UNITED STATES PATENT AND TRADEMARK OFFICE

Patent Application Serial No. 09/921,518
Filing Date August 1, 2001
Inventor John T. Moore
Assignee Micron Technology, Inc.
Group Art Unit 2818
Examiner Phuc T. Dang
Attorney Docket No. MI22-1669
Title: Method of Forming Integrated Circuitry, Method of Forming Memory
Circuitry, and Method of Forming Random Access Memory Circuitry

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

References -- See Attached Form PTO-1449


The attached form PTO-1449 is submitted in compliance with 37 C.F.R. §1.56. Copies of the cited art are included. No admission is made regarding whether all the submitted references are prior art.

This Supplemental Information Disclosure Statement is being filed before the mailing of a first Office Action following the filing of a Request for Continued Examination. Therefore, no fee is believed to be required per 37 C.F.R. § 1.97(b)(4). However, in the event that a fee is required for filing this Supplemental Information Disclosure Statement, please charge the fee specified under 37 C.F.R. § 1.17(p) to Deposit Account No. 23-0925.

Respectfully submitted,

Dated: 10-9-02Attorney: [Signature]
Mark S. Matkin
Reg. No. 32,268



Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE			ATTY. DOCKET NO. MI22-1669		SERIAL NO. 09/921,518	
					ART OF ART CITED BY APPLICANT (Use several sheets if necessary)			
					APPLICANT: John T. Moore			
					FILING DATE August 1, 2001		GROUP 2818	
U.S. PATENT DOCUMENTS								
*Examiner Initial	AA	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
	AA	3,622,319	11/23/71	Sharp	96	27		
	AB	3,743,847	07/03/73	Boland	250	510		
	AC	4,269,935	05/26/81	Masters et al.	430	323		
	AD	4,312,938	01/26/82	Drexler et al.	430	496		
	AE	4,320,191	03/16/82	Yoshikawa et al.	430	296		
	AF	4,795,657	01/03/89	Formigoni et al.	427	96		
	AG	4,847,674	07/11/89	Silwa et al.	357	67		
	AH	5,177,567	01/05/93	Klersy et al.	257	4		
	AI	5,219,788	06/15/93	Abernathy et al.	437	187		
	AJ	5,751,012	05/12/98	Wolstenholme et al.	257	5		
FOREIGN PATENT DOCUMENTS								
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							Yes	No
	AK							
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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)								
	AN		Das et al., <i>Theory of the characteristic curves of the silver chalcogenide glass inorganic photoresists</i> , 54 APPL. PHYS. LETT., No. 18, pp. 1745-1747 (May 1989).					
	AO		Helbert et al., <i>Intralevel hybrid resist process with submicron capability</i> , SPIE Vol. 333 SUBMICRON LITHOGRAPHY pp. 24-29 (1982)					
	AP		Hilt, DISSERTATION: <i>Materials Characterization of Silver Chalcogenide Programmable Metallization Cells</i> , Arizona State University, pp. title page-114 (UMI Company, May 1999).					
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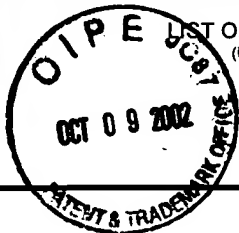
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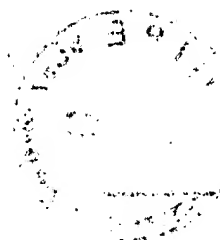
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*Examiner Initial	AA	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
	AA	5,789,277	08/04/98	Zahorik et al.	438	95	
	AB	5,841,150	11/24/98	Gonzalez et al.	257	3	
	AC	5,920,788	07/06/99	Reinberg	438	466	
	AD	5,998,066	12/07/99	Block et al.	430	5	
	AE	6,077,729	06/20/00	Harshfield	438	128	
	AF	6,236,059 B1	05/22/01	Wolstenholme et al.	257	3	
	AG	6,297,170 B1	10/02/01	Gabriel et al.	438	738	
	AH	6,300,684 B1	10/09/01	Gonzalez et al.	257	774	
	AI	6,316,784 B1	11/13/01	Zahorik et al.	257	3	
	AJ	6,329,606 B1	12/11/01	Freyman et al.	174	260	
	AK	6,348,365	02/19/02	Moore et al.	438	130	
FOREIGN PATENT DOCUMENTS							
		Document Number	Date	Country	Class	Subclass	Translation
							Yes No
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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)							
	AN		Holmquist et al., <i>Reaction and Diffusion in Silver-Arsenic Chalcogenide Glass Systems</i> ,				
			62 J. AMER. CERAMIC SOC., Nos. 3-4, pp. 183-188 (Mar.-Apr. 1979).				
	AO		Huggett et al., <i>Development of silver sensitized germanium selenide photoresist by reactive</i>				
			<i>sputter etching in SF₆</i> , 42 APPL. PHYS. LETT., No. 7, pp. 592-594 (April 1983).				
	AP		Kawaguchi et al., <i>Mechanism of photosurface deposition</i> , 164-166 J. NON-CRYST. SOLIDS,				
			pp. 1231-1234 (1993).				
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	AA	6,376,284 B1	04/23/02	Gonzalez et al.	438	129	
	AB	6,391,688 B1	05/21/02	Gonzalez et al.	438	128	
	AC	6,414,376 B1	07/02/02	Thakur et al.	257	640	
	AD	6,418,049 B1	07/09/02	Kozicki et al.	365	174	
	AE	6,423,628 B1	07/23/02	Li et al.	438	622	
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	AN		McHardy et al., <i>The dissolution of metals in amorphous chalcogenides and the effects of electron and ultraviolet radiation</i> , 20 J. PHYS. C: SOLID STATE PHYS., pp. 4055-4075 (1987).				
	AO		Miyatani, <i>Electrical Properties of Ag₂Se</i> , 13 J. Phys. Soc. Japan, p. 317 (1958).				
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AA	10/061,825		Gilton et al. (as filed and amended)			01/31/2002
AB	10/077,867		Campbell et al. (as filed)			02/20/2002
AC	10/232,757		Li, et al. (as filed)			08/29/2002
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	AN		Owens et al., <i>Metal-Chalcogenide Photoresists for High Resolution Lithography and Sub-Micron Structures</i> , NANOSTRUCTURE PHYSICS AND FABRICATION, pp. 447-451 (Academic Press, 1989).			
	AO		Safran et al., <i>TEM study of Ag₂Se developed by the reaction of polycrystalline silver films and selenium</i> , 317 THIN SOLID FILMS, pp. 72-76 (1998).			
	AP		Shimizu et al., <i>The Photo-Erasable Memory Switching Effect of Ag Photo-Doped Chalcogenide Glasses</i> , 46 BUL. CHEM. SOC. JAPAN, No. 12, pp. 3662-3665 (December 1973).			
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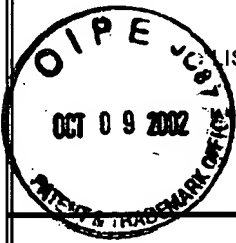
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			NaCl and SiO _x Substrates, 74 ACTA PHYSICA HUNGARICA, No. 3, pp. 243-255 (1994).				
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			pp. 32-39 (March 1982).				
	AP		Tai et al., <i>Submicron optical lithography using an inorganic resist/polymer bilevel scheme</i> ,				
			17 J. Vac. Sci. Technol., No. 5, pp. 1169-1176 (Sept./Oct. 1980).				
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	AP		Yoshikawa et al., <i>A new inorganic electron resist of high contrast</i> , 31 APPL. PHYS. LETT., No. 3, pp. 161-163 (August 1977).			
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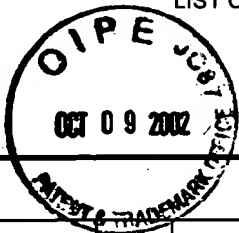
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	AN		Yoshikawa et al., <i>Dry development of Se-Ge Inorganic photoresist</i> , 36 APPL. PHYS. LETT., No. 1, pp. 107-109 (January 1980).				
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